



# 406-512 MHz POWER AMPLIFIER BOARD 19D423928G5, G6, G8

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### DESCRIPTION

The PA assembly for CUSTOM MVP transmitters uses four RF power transistors to provide a power output of 35 Watts. The output power is adjustable using power control R213 and is type accepted with the FCC to operate over a range of 1-Watt to rated output power. A single transistor is used in the power control circuit.

Supply voltage (A+) for the PA is connected from J1 on the back of the radio through FL210-C5 on the side of the radio. C201, C202, and C203 prevent RF from getting on the power leads. Diode CR201 will cause the main fuse assembly to blow if the polarity of the power leads is reversed, providing reverse voltage protection for the radio.

Centralized metering jack J5 is provided for use with GE Test Set Model 4EX3A11 or Test Kit 4EX8K12. The Test Set meters the Ampl-1 drive (exciter output), power adjust voltage, driver, and PA current.

### CIRCUIT ANALYSIS

#### RF POWER AMPLIFIERS

The exciter output is coupled through RF cable W201 to PA input jack J1. The 50 ohms RF input is coupled through a matching network comprised of C6, C7, C8 and W2 to the base of power amplifier Q1.

Part of the RF input is rectified by CR1 and metered at J5-4 through resistor R1.

Collector voltage for Ql is applied direct from the DC power input through collector stabilizing network R5 and L2 and collector feed network L3 and C10.

The output of Q1 is coupled to the base of a second power amplifier Q202 through a matching network consisting of T1, C15 and C16.

Collector voltage to Q202 is controlled by power control circuit, Q215, and is applied through a collector stabilizing network L6 and R6 and collector feed network L5 and C18.

The output of Q202 is coupled to the base of driver Q203 through C17, C19 and a matching network consisting of T2, C22, C52, C24 and C25. The collector voltage to

Q203 is coupled through collector stabilizing network L9 and R14 and collector feed network L8 and C26.

Collector current for Q203 is metered across tapped manganin resistor R12. The reading is taken in position F on the 1-Volt scale with the High Sensitivity button pressed, and read as 0-15 amperes full scale.

The output of driver Q203 is coupled through an impedance matching network (C26, C27, C29, C30, C33 and T3) that matches the output impedance of Q203 to the input impedance of power amplifier Q204 through a 50 ohm micro strip (W204) and input impedance matching network T4, C34, C35 and C36.

Collector current for Q204 is metered across tapped manganin resistor R10. The reading is taken in position G on the 1-Volt scale with the High Sensitivity button pressed and read as 0-15 amperes full scale.

Following power amplifier Q204 is a matching network C37, C38, and T5 that matches the output of Q204 to the 50-ohm input of low pass filter, through 50 ohm micro strip W5 and a 50 ohm cable W214. C1 on the low pass filter board provides DC isolation between the transmitter and the antenna.

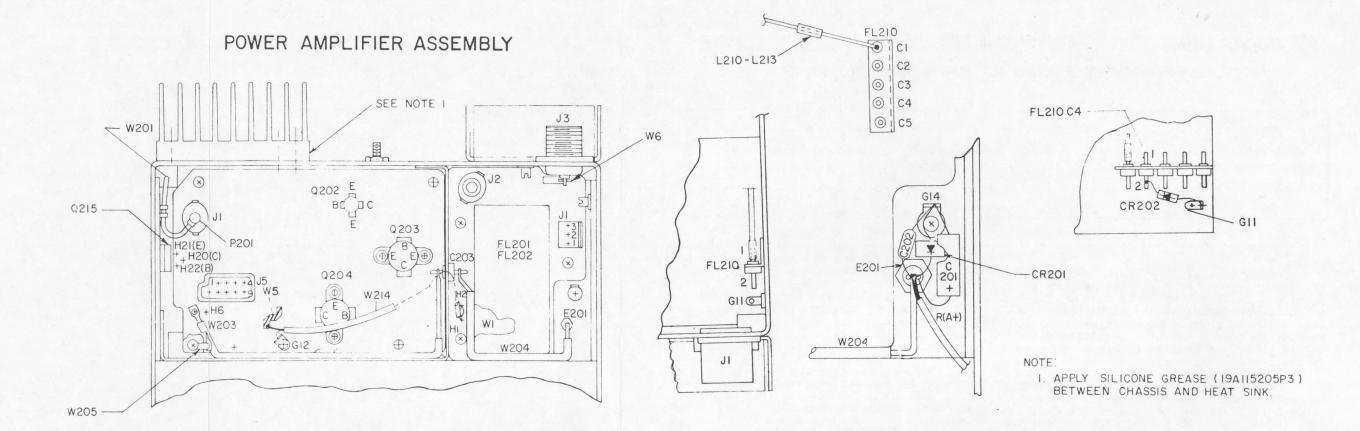
The PA output is coupled through the low-pass filter to the antenna through antenna transfer relay K1.

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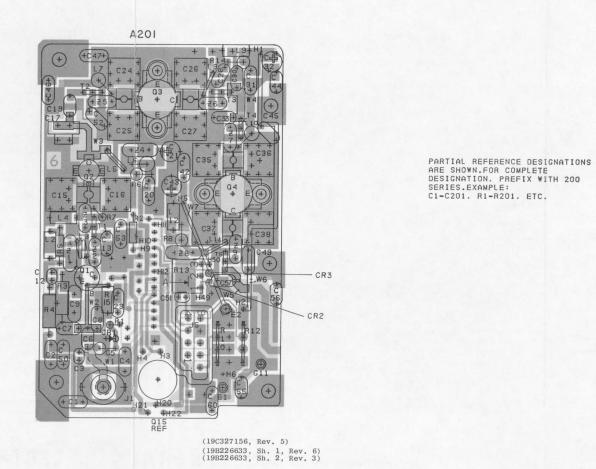
The RF Power Transistors used in the transmitter contain Beryllium Oxide, a TOXIC substance. If the ceramic, or other encapsulation is opened, crushed, broken or abraded, the dust may be hazardous if inhaled. Use care in replacing transistors of this type.

## POWER CONTROL CIRCUIT

The power control circuit consists of R13 and Q215. R13 controls the base voltage, and conduction of Q215. Q215 is connected in series with the collector feed network for Q202 thereby controlling the drive to Q203 and therefore the output power. R13 is adjusted to provide the desired output power. The control voltage for Q202 is measured in position C on 1 volt scale and read as 0-15 volts full scale.



(19C327852, Rev. 3)



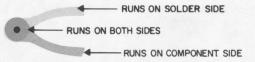
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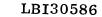
OUTLINE DIAGRAM

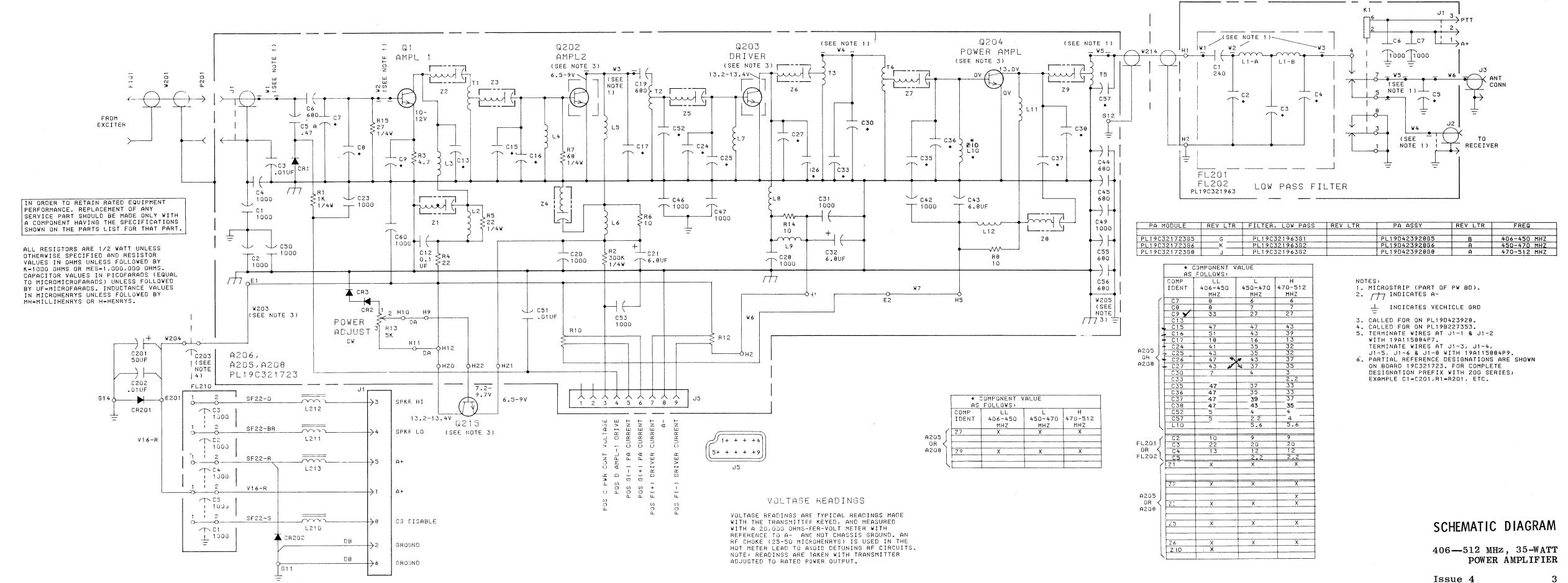
406—512 MHz, 35-WATT POWER AMPLIFIER

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Issue 5







LBI30586

\*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES.

LBI30586			SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	
		PARTS LIST		<u> </u>								1		1							01
		LB130585D	C216LL	19A116952P51	Metallized teflon: 51 pf ±2%, 250 VDCw.	C236LL*	19A116952P47	Metallized teflon: 47 pf ±2%, 250 VDCW; sim to Underwood Type JlHF.	C252L and	19A116656P4J0	Ceramic disc: 4 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.	R213	19A116559P102	Variable, cermet: 5K ohms ±20%, .5 w; sim to CTS Series 360.						JACKS AND RECEPTACLES	Changes Letter," v previous
	406-51	2 MHz 35 WATT POWER AMPLIFIER 19D423928G5 406-450 MHz	C216L	19A116952P43	Metallized teflon: 43 pf ±2%, 250 VDCw.			In REV F & earlier:	С252Н			R214	19A700113P15	Composition: 10 ohms ±5%, 1/2 w.	C201	19A115680P4	Electrolytic: 50 µf +150% -10%, 25 VDCw; sim to Mallory Type TTX.	J1		Connector, Includes:	previous
		19D423928G6 450~470 MHz 19D423928G8 470~512 MHz	C216H	19A116952P39	Metallized teflon: 39 pf ±2%, 250 VDCW.		19A116952P39	Metallized teflon: 39 pf ±2%, 250 VDCw; sim	C253	19A116655P20	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	R215	19A700106P25	Composition: 27 ohms ±5%, 1/4 w.	C202	19A116080P101	Polyester: 0.01 µf ±10%, 50 VDCW.		19A115884P12	Shell.	REV. A
			C217LL C217L	19A116679P18D 19A116679P16D	Metallized teflon: 18 pf ±.5 pf, 250 VDCW.  Metallized teflon: 16 pf ±.5 pf, 250 VDCW.	C236L	19A116952P35	to Underwood Type JlHF.  Metallized teflon: 35 pf ±2%, 250 VDCw; sim	C255 and	19A116655P18	Ceramic disc: 680 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.			TRANS FORMERS	C203	19B209488P2	Ceramic, feed-thru: 1000 pf +100% -0%, 500 VDCW;		19A115884P7	Contacts, male: wire size 14-20; sim to AMP 60528-1.	REV. E
SYMBOL	GE PART NO.	DESCRIPTION	C217H	19A116679P13D	Metallized teflon: 13 pf ±.5 pf, 250 VDCw.	C250E	133110302130	to Underwood Type JlHF.	C256	10.11.005.005.10	Garagia dia a E of 10 E of 500 VDON town coof	T201	19A130446G1	Coil.			sim to Allen-Bradley Style FA5D.		19A115884P9	Contacts, male: wire size 22-30; sim to AMP 60910-1.	REV. E
SIMIDUL	GETAKT NO.	DESCRIPTION	C218*	19A134666P1	Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted in G5 by REV F.	С236Н	19A116952P33	Metallized teflon: 33 pf ±2%, 250 VDCw; sim to Underwood Type JlHF.	C257LL	19A116656P5J0	Ceramic disc: 5 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.	thru T205					DIODES AND RECTIFIERS	J3	19A700067P1	Connector, receptacle: coaxial; sim to Amphenol 83-798.	REV. E
A 2.05		POWER AMPLIFIER MODULE				C237LL*	19A116952P47	Metallized teflon: 47 pf ±2%, 250 VDCW; sim to Underwood Type JlHF.	C257H*	19A116656P4J0	Ceramic disc: 4 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.			CABLES	CR201	19A116783P1 4037822P1	Silicon, 100 VDC blocking, 6 amps.				REV. E
A205, A206, A208		A205 19C321723G5 406-450 MHz A206 19C321723G6 450-470 MHz	C219	19A116655P18	Ceramic disc: 680 pf ±10%, 1000 VDCw; sim to RMC Type JF Discap.			In REV E & F:			In REV H & earlier;	W201 thru		(Part of printed board 19D423005P1).	CR202	403762221	Silicon, 1000 mA, 400 PIV.	1			REV. F
		A208 19C321723G8 470-512 MHz	C220	19A116655P20	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.		19A116952P51	Metallized teflon: 51 pf ±2%, 250 VDCW; sim to Underwood Type J1HF.		19A134100P20	Ceramic disc: 2.2 pf ±0.1 pf, 100 VDCW.	W204 W206	19B226971G1	Jumper.				thru L213	19A126140P3	Core, toroidal, ferrite: sim to Stackpole 88-31959.	REV. F
			C221	19A134202P15	Tantalum: 6.8 μf ±20%, 35 VDCW.			In REV D & earlier:	C260	19A116655P20	Ceramic disc: 1000 pf $\pm 10\%$ , 1000 VDCW; sim to RMC Type JF Discap.	W207	19A130791G1	Jumper.	E201	7143206P1	Terminal, standoff.	12.10			REV. G
C201 and	19A116655P20	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C222LL*	19A116656P33J0	Ceramic disc: 33 pf ±5%, 500 VDCw, temp coef 0 PPM. Deleted by REV F.		19A116952P47	Metallized teflon: 47 pf ±2%, 250 VDCW; sim to Underwood Type J1HF.			DIODES AND RECTIFIERS				1			P201		(Part of W201).	REV. A
C202 C203	19A116192P1	Ceramic: 0.01 µf ±20%, 50 VDCW; sim to Erie	C222L*	19A116656P24J0	Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef	C237L*	19A116952P39	Metallized teflon: 39 pf ±2%, 250 VDCW; sim to	CR201	19A116052P1	Diode, hot carrier: Fwd. drop .350 v. max.	Z2011.1.*	* 19A134666P3	Network, Freq. Selective; sim to Dilectron TC501;	FL201 and		FLLTER BOARD FL201 19C321963G1 406-450 MHz (LL) FL202 19C321963G2 450-512 MHz (H)				REV. A
		8121 SPECIAL.	and C222H*		O PPM. Deleted in G6 by REV H. Deleted in G8 by REV G.			Underwood Type JlHF.	CR202	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.			NPO:240j:SLAC. Added by REV F.	FL202		F1202 13032130302 430 312 Mile (II)	Q202	19A134164P2	Silicon, NPN; sim to Type 2N5945.	REV. F
C204	19A116655P20	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C223	19A116655P20	Ceramic disc; 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.		19A116952P47	In REV H & earlier;  Metallized teflon: 47 pf ±2%, 250 VDCW; sim to	CR203			Z201L*	19A134663P1	Network, Freq. Selective; sim to Dilectron TC501; NPO:240J:SLAC. Added by REV H.				Q203C	19A134239P3	Silicon, NPN. (406-450 MHz)	REV. H
C205	19A700013P9	Phenolic; 0.47 pf ±5%, 500 VDCW.	C224IL	19A116952P41	Metallized teflon: 41 pf ±2%, 250 YDCw.			Underwood Type J1HF.	F.1	104124262D1	Contact, electrical; sim to Selectro X-L-070174-1.	Z201H*	19A134666P1	Network, Freq. Selective; sim to Dilectron TC501: NPO:240J:SLaC. Added by REV G.	C2LL	19A700015P38 19A700014P4	Teflon/mica: 240 pf ±5%, 250 VDCW.  Teflon/mica: 10 pf ±5%, 250 VDCW.	Q203D	19A134239F1	Silicon, NPN. (450-512 MHz)	REV. G
C206	19A116655P18	Ceramic disc: 680 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C224L	19A116952P35	Metallized teflon: 35 pf ±2%, 250 VDCW.	C237H*	19A116952P37	Metallized teflon: 37 pf ±2%, 250 VDCW; sim to Underwood Type J1HF.	and E2	19A134263P1	Contact, electrical, Sim to Solice vio in 2 ordination	Z202LL*	▶ 19A134666P3	Network, Freq. Selective; sim to Dilectron TC501: NPO: 330J:SLAC. Added by REV F.	С2Н	19A116952P9	Metallized teflon: 9 pf ±0.5 pf, 250 VDCW.	Q204	19A134242F1 19A116742F1	Silicon, NPN. Silicon, NPN.	REV. J
C207LL	19A116656P8J0	Ceramic disc: 8 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.	С224Н	19A116952P32	Metallized teflon: 32 pf ±2%, 250 VDCw.			In REV D & earlier:	G11	19A134263P1	Contact, electrical; sim to Selectro X-L-070174-1.	Z202L*	19A134666P1	Network, Freq. Selective; sim to Dilectron TC501:	C3LL	19A116952P22	Metallized teflon: 22 pf ±0.5 pf, 250 VDCW.	Q215	19811074221		REV. H
C207L	19A116656P6J0	Ceramic disc: 6 pf ±0.5 pf, 500 VDCW, temp coef	C225LL	19A116952P43	Metallized teflon: 43 pf ±2%, 250 VDCW.  Metallized teflon: 35 pf ±2%, 250 VDCW.		19A116952P33	Metallized teflon: 33 pf $\pm 2\%$ , 250 VDCW; sim to Underwood Type JlHF.						NPO:240J:SLAC. Added by REV H.	СЗН	19A116952P20	Metallized teflon: 20 pf ±0.5 pf, 250 VDCW.			CABLES CABLES	
and C207H		О РРМ.	C225L C225H	19A116952P35 19A116952P32		C238LL*	19A116952P47	Metallized teflon: 47 pf ±2%, 250 VDCW; sim to Underwood Type J1HF.	J201	19A130924G1	Connector, coaxial: jack type; sim to Cinch	Z202H*	19A134666P1	Network, Freq. Selective; sim to Dilectron TC501: NPO:240J:SLAC. Added by REV G.	C4ILL	19A116952P13	Metallized teflon: 13 pf ±0.5 pf, 250 VDCW.	w201*	19A130909G1	Cable, RF: approx 7-1/2 inches long. Earlier than REV A:	REV. G
C208LL	19A116656P8J0	Ceramic disc: 8 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.	C226LL	1	Metallized teflon: 47 pf ±2%, 250 VDCW.			In REV E & F:		10001005461	14H11613. Connector: 9 contacts.	Z203LL*	* 19A134666P3	Network, Freq. Selective; sim to Dilectron TC501: NPO:330J:SLAC. Added by REV F.	C4H C5H	19A116952P12 19A134100P20	Metallized teflon: 12 pf ±0.5 pf, 250 VDCW.  Ceramic: 2.2 pf ±0.1 pf, 100 VDCW.		5491689P91	Cable, kF: approx 7-1/2 inches long.	
C208L*	19A116656P7J0	Ceramic disc: 7 pf ±0.5 pf, 500 VDCW, temp coef	C226L	19A116952P43	Metallized teflon: 43 pf ±2%, 250 VDCW.		19A116952P51	Metallized teflon: 51 pf ±2%, 250 VDCW; sim to Underwood Type JlHF.	J205	19B219374G1	Connector. 9 contacts.	Z203L*	19A134636P1	Network, Freq. Selective; sim to Dilectron TC501: NPO: 240J:SLAC. Added by REV H.	C6	19A116655P20	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to	w203	19C327146F1	Jumper.	REV. B
		O PPM.						blidelwood 15pc bint.				Z203H*	19A134636P1	Network, Freq. Selective; sim to Dilectron TC501:	and C7		RMC Type JF Discap.				
												1 220011	10,110,100,000	NPO: 240J; SLAC. Added by REV G.							REV. K
			С226Н	19A116952P37	Metallized teflon: 37 pf ±2%, 250 VDCw.			In REV D & earlier:			INDUCTORS	g004#	19A134666P1	Network, Freq. Selective; sim to Dilectron TC501:				w204	19C327146F2	Jumper.	REV. J
		In REV F & earlier:	C227LL	19A116952P43	Metallized teflon: 43 pf ±2%, 250 VDCw.		19A116952P47	Metallized teflon: 47 pf ±2%, 250 VDCW; sim	1,202	19A129773G1	Coil.	Z204*	194134600F1	NPO: 240J: SLAC. Added to G5 by REV F. Added to G6 by REV H. Added to G8 by REV G.			JACKS AND RECEPTACLES	W205	7135118P1	Terminal, solder.	
	19A116656P6J0	Ceramic disc: 6 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.	C227L	19A116952P37	Metallized teflon: 37 pf ±2%, 250 VDCW.		104110050740	to Underwood Type JlHF.  Metallized teflon: 43 pf ±2%, 250 VDCW; sim to	L203	19A129774P1	Coil.	Z205LL*	* 19A134666P3	Network, Freq. Selective; sim to Dilectron TC501: NPO: 3301: SLAC. Added by REV F.	J1	19A116659P55	Connector, printed wiring: 3 contacts; sim to Molex 09-65-1031.	W214	19A130831C2	Cable: approx 5-1/4 inches long.	
C208H*	19A116656P7J0	Ceramic disc: 7 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.	С227Н	19A116952P35	Metallized teflon: 35 pf ±2%, 250 VDCW.	C238L*	19A116952P43	Underwood Type JlHF.	L204	19A129773G1	Coil.	Z205L*	19A134666P1	Network, Freq. Selective; sim to Dilectron TC501;	J2	19A130924G1	Connector, coaxial: jack type; sim to Cinch 14H11613.			MISCELLANEOUS	
		In REV E & earlier:	C228	19A116655P20	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.			In REV H & earlier:	L205	19B219457P6 19A700000P120	Coil.  Choke, RF: 5.6 \( \mu \)h \( \pm \)10%, 0.13 ohms DC res max.	220011		NPO: 240j: SLAC. Added by REV H.					19C32784661	Heat sink, finned. Insulator. (Located under A205 & A206, A208).	
	19A116656P6J0	Ceramic disc: 6 pf ±0.5 pf, 500 VDCW, temp coef	C229LL*	19A116656P33J0	Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef 0 PPM. Deleted by REV F.		19A116952P47	Metallized teflon: 47 pf $\pm 2\%$ , 250 VDCW; sim to Underwood Type JlHF.	L206 L207	19A700000P20	Choke, RF: $5.6 \mu h \pm 10\%$ , 0.28 ohms DC res max.	Z205H*	19A134666P1	Network, Freq. Selective; sim to Dilectron TC501: NPO: 240J: SLAC. Added by REV G.					19C321441F1 19B227353G1	Shield. (Located around A205, A206, A208).	
C2091LL	19A116656P33J0	0.0704	C229L*	19A116656P24J0	Coramic disc: 24 pf ±5%, 500 VDCW, temp coef	C238H*	19A116952P35	Metallized teflon: 35 pf ±2%, 250 VDCW; sim to Underwood Type JlHF.	L208LL	19B219457P6	Coil.	Z206LL	* 19A134666P3	Network, Freq. Selective; sim to Dilectron TC501: NPO:330J:SLAC. Added by REV F.	K1	19A700061P1	Hermetic sealed: 180-341 ohms coil res, 8-16.3 VDC; sim to GE 3SAV1760A2 or Potter-Brunfield HCM6160.		19B201074P304	Tap screw, Phillips POZIDRIV®: No. 6-32 x 1/4.	
C209L	19A116656P27J0	TOO	l Ia		REV G.			In REV E-G:	L208L and	19A130650P1	Coil.	Z206L*	19A134666P1	Network, Freq. Selective; sim to Dilectron TC501: NPO: 2400: SLaC. Added by REV H.				i <b>I</b>	19B201074F305	(Secures shield to frame at C17).  Tap screw, Phillips POZIDRIV®: No. 6-32 x 5/16.	1
С209Н	19A116656P27J0	Ceramic mica: 27 pf ±5%, 500 VDCW, temp coef 0 PPM.	C230LL*	19A116656P7J0	Ceramic disc: 7 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.	1	19A116952P39	Metallized teflon: 39 pf ±2%, 250 VDCW; sim to Underwood Type JlHF.	L208H			Z206H*	19A134666P1	Network, Freq. Selective; sim to Dilectron TC501:	.,,,,	10000704001	INDUCTORS Jumper.		1982010747303	(Secures shield to frame at J5).	,
C210LL*	19A134666P3	Silver mica: 27 pf ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV F.			In REV F & earlier:			In REV D & earlier:	L209	19A129773G1	Coil.  Choke, RF: 15.0 $\mu$ h $\pm$ 10%, 1.20 ohms DC res max.	11		NPO: 240j; SLAC. Added by REV G.	L1H	19B227240P1 19B227240P2	Jumper.		5492178P2	Washer, spring tension. (Used with Q202).	i
C210L*	19A134666P1	Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted in G6 by REV H.		19A116656P6J0	Ceramic disc: 6 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.		19A116952P35	Metallized teflon: 35 pf ±2%, 250 VDCW; sim to Underwood Type J1HF.	L210LL		Deleted by REV G.	Z207LL	* 19A134666P3	Network, Freq. Selective; sim to Dilectron TC501: NPO:330J:SLAC. Added by REV F.					N207P15C6 19A130465F1	Hex nut: No. 8-32. (Used with Q202).  Spacer. (Used with Q202).	ı
and C210H*		Deleted in G8 by REV G.	C230L	19A116656P4J0	Ceramic disc: 4 pf ±0.5 pf, 500 VDCW, temp coef	C239*	19A116666P1	Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted in G5 by REV F.	L210L and		Choke, RF: 5.6 μh ±10%, 0.28 ohms DC res max.	Z207L*	19A134666P1	Network, Freq. Selective; sim to Dilectron TC501: NPO:240J:SLAC. Added by REV H.	W1		(Part of printed board 19C321962P1).		N44P9006C6	Screw, machine: No. 4-40 x 3/8. (Secures Q203).	ı
C211LL*	19A116656P33J0	Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef 0 PPM. Deleted by REV F.	С230Н	19A116656P3J0	O PPM.  Ceramic disc: 3 pf ±0.5 pf, 500 VDCW, temp coef			Motive Type DM154CR. Deleted in G5 by REV F. Deleted in G6 by REV H. Deleted in G8 by REV G.	L210H L211	19B219457P6	Coil.	Z207H*	19A134666P1	Network, Freq. Selective; sim to Dilectron TC501; NPO:240J; SLAC. Added by REV G.	thru W5				19A116023P1	Insulator, plate. Dupont No. 300 Kapton H. (Located under Q215).	i
C211L*	19A116656P24J0	Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef 0 PPM. Deleted in G6 by REV H. Deleted in G8	C230H		O PPM.	C240LL*	19Al16656P33J0	Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef O PPM. Deleted by REV F.	L212	19A129773G1	Coil.	Z208*	19A134666P1	Notwork From Selective: sim to Dilectron TC501;	₩6	19A136512P1	Antenna strap.		19A134016P1	Insulator, bushing. (Used with Q215).	1
C211H*		by REV G.  Ceramic: 0.01 µf ±20%, 50 VDCW; sim to Erie 8121	C231	19A116655P20	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C240L*	19A116656P24J0	Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef 0 PPM. Deleted in G6 by REV H. Deleted in G8 by			TRANSISTORS	2200	10.110,2000-1	NPO:240J:SLAC. Added to G5 by REV F. Added to G6 by REV H. Added to G8 by REV G.	į				7878243P11	Hex nut: No. 8-32. (Secures stud that mates with wing nut securing radio to case).	i
C212	19A116192P1	SPECIAL.	C232	19A134202P15	Tantalum: 6.8 μf ±20%, 35 VDCw.	and C240H*		REV G.	Q201	19A134237P1	Silicon, NPN.	Z20911	* 19A134666P3	Network, Freq. Selective; sim to Dilectron TC501: NPO:330J:SLAC. Added by REV F.	FL210		FILTER 19A136680G1		4033714P11	Terminal, solderless: sim to Zierick 349.	ı
C213*	19A116656P4J0	Ceramic disc: 4 pf ±0.5 pf, 500 VDCw, temp coef 0 PPM. Deleted by REV G.	С233Н	19A134100P20	Ceramic disc: 2.2 pf ±0.1 pf, 100 VDCW, temp coef 0 ±120PPM/*C.	C242	19A116655P20	Ceramic disc: 1000 pf $\pm 10\%$ , 1000 VDCw; sim to RMC Type JF Discap.			RESISTORS	Z209L*	19A134666P1	Network, Freq. Selective; sim to Dilectron TC501;					403311111	(Solders to FL201 & FL202).	i
C214LL*	19A116656P33J0	Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef 0 PPM. Deleted by REV F.	C234LL*	19A116656P33J0	Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef 0 PPM. Deleted by REV F.	C243	19A134202P15	Tantalum: 6.8 µf ±20%, 35 VDCW.	R201	19A700106P63	Composition: 1K ohms ±5%, 1/8 w.			NPO: 240J: SLAC. Added by REV H.  Network, Freq. Selective; sim to Dilectron TC501:					N84P13003C6	Tap screw, Phillips Pozidriv®: No. 6-32 x 3/16. (Secures FL210).	1
C214L*	19A116656P24J0	Goramic disc: 24 nf ±5%, 500 VDCW, temp coef	C234L*	19A116656P24J0	Garagia disa: 24 pf +5% 500 VDCW temp coef	C244 and	19A116655P18	Ceramic disc: 680 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	R201	3R152P304J	Composition: 300K ohms ±5%, 1/4 w.	Z209H*	19A134666P1	NPO:240J;SLAC. Added by REV G.	Cl thru	5493392P7	Ceramic, feed-thru: 1000 pf +100% -0%, 500 VDCW; sim to Allen-Bradley Type FA5C.		19B201074P204	Tap screw, Phillips POZIDRIV®: No. 4-40 x 1/4. (Secures J3).	1
and C214H*	151500012100	O PPM. Deleted in G6 by REV H. Deleted in G8 by REV G.	and C234H*		O PPM. Deleted in G6 by REV H. Deleted in G8 by REV G.	C245		Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to	R203	19A700113P7	Composition: 4.7 ohms ±5%, 1/2 w.	Z210*		Network. Added by REV G. Includes:	C5				4036555Pl	Insulator, washer: nylon. (Used with Q201 on	i
C215LL	19A116952P47	Metallized teflon: 47 pf ±2%, 250 VDCW.	C235LL*	19A116952P47	Metallized teflon: 47 pf ±2%, 250 VDCW; sim to Underwood Type JlHF.	C246 and C247	19A116655P20	RMC Type JF Discap.	R204	19A700113P23	Composition: 22 ohms ±5%, 1/2 w.	L1	19A700024P1	Coil, RF: 100 nH ±10%, 0.08 ohms DC res max.	G11	7135118P2	Terminal, solderless.		19B219554G2	PA Module).  Can. (FL201, FL202).	1
and C215L					In REV F & earlier:	C247 C249	19A116655P20	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to	R205	19A700106P23	Composition: 22 ohms ±5%, 1/4 w.  Composition: 10 ohms ±5%, 1/2 w.	L2	19A129773G1 19A700106P15	Resistor, composition: 10 ohms ±5%, 1/4 w.	and G12				19B219554G2	Cover. (FL201, FL202).	1
C215H	19A116952P43	Metallized teflon: 43 pf ±2%, 250 VDCW.		19A116952P43	Metallized teflon: 43 pf ±2%, 250 VDCW; sim to Underwood Type JlHF.	and C250		RMC Type JF Discap.	R206 R207	19A700113P15 19A700106P35	Composition: 68 ohms ±5%, 1/4 w.				G14	7135118P2	Terminal, solderless.		19B209502P1	Terminal, stud. (Used with C2, C3, C4).	1
			C235L	19A116952P37	Metallized teflon: 37 pf ±2%, 250 VDCW; sim	C251	19A116192P1	Ceramic: 0.01 $\mu$ f $\pm 20\%$ , 50 VDCW; sim to Erie 8121 SPECIAL.	R207	19A700113P15	Composition: 10 ohms ±5%, 1/2 w.								19A116417P4	Bumper, plastic. (Quantity 4).	1
				10411/050000	to Underwood Type JiHF.	C252LL	19A116656P5J0	Ceramic disc: 5 pf ±0.5 pf, 500 VDCW, temp coef	R210	19C320212P1	Shunt resistor.						·				1
4			C235H	19A116952P33	Underwood Type JiHF.			O PPM.	R212	19C320212P1	Shunt resistor.										1
7			·	•				<u> </u>	- L			<u> </u>	<u> </u>						<del></del>		

PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter," which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

- REV. A D Power Amplifier Module 19C321723G5, 6, 8

  REV. E Power Amplifier Module 19C321723G6

  Incorporated in initial shipment.

  REV. E Power Amplifier Module 19C321723G5

  Increase Power output. Changed C237LL and C238LL.
- REV. F Power Amplifier Module 19C321723G8
  Increase Power output. Changed C237H and C238H.

  REV. F Power Amplifier Module 19C321723G6
- To improve operation. Changed C209L.

  REV. F Power Amplifier Module 19C321723G8
- REV. G Power Amplifier Module 19C321723G6
  To input VSWR. Changed C208L and C208H.
- REV. A Power Amplifier Assembly 19D423928G5, G6, G8

  To reduce power fluctuations when cable is re-positioned. Changed W201.
- REV. F Power Amplifier Module 19C321723G5
- REV. H Power Amplifier Module 19C321723G6
  REV. G Power Amplifier Module 19C321723G8
  - To incorporate frequency selective networks. Replaced Cl0, Cl1, Cl4, Cl8, C22, C29, C34, C39 and C40 with Zl through Z9.
- REV. J Power Amplifier Module 19C321723G6

  REV. H Power Amplifier Module 19C321723G8

  To increase power output in 450-512 MHz range. Changed C237L, C238L and C238H.
- C238L and C238H.

  REV. G Power Amplifier Module 19C321723G5

  To increase power output in 406-450 MHz range. Deleted C213 and C210LL. Changed C230LL, C235LL, C236LL, C237LL, C238LL and added Z210LL.
- REV. B Power Amplifier Assembly 19D423928G5
- To increase power output in 406-450 MHz range. Changed Q203C.

  REV. K Power Amplifier Module 19C321723G6
- To increase power output in 450-470 MHz range. Added C257M.
- REV. J Power Amplifier Module 19C321723G8

  To increase power output in 470-512 MHz range. Changed C257H.